

A cross-sectional view of a semiconductor device. The device consists of a substrate 101 with a thin layer 102 on top. A grid structure is formed on top of the substrate, comprising a series of rectangular openings 104 separated by vertical walls 106. The grid is made of a material 108, and the openings are filled with a material 107. The top surface of the grid is labeled 111, and the side walls are labeled 112. The bottom surface of the grid is labeled 113. The top surface of the substrate is labeled 114.

FIG. 1C

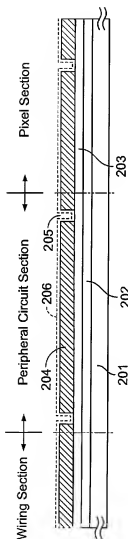


FIG. 2A

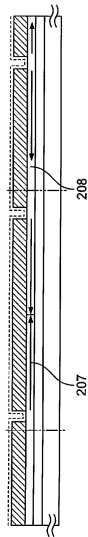


FIG. 2B

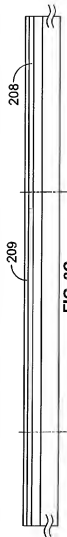


FIG. 2C

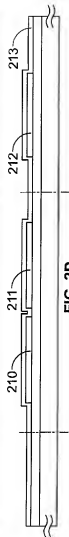
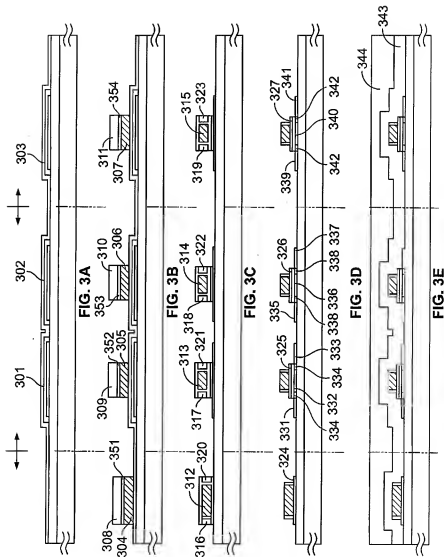


FIG. 2D



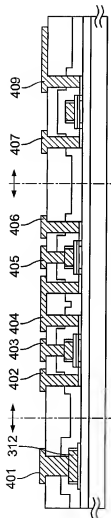


FIG. 4A

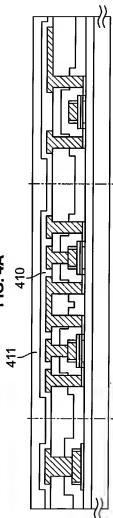


FIG. 4B

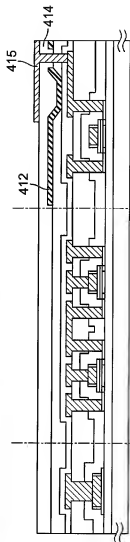


FIG. 4C

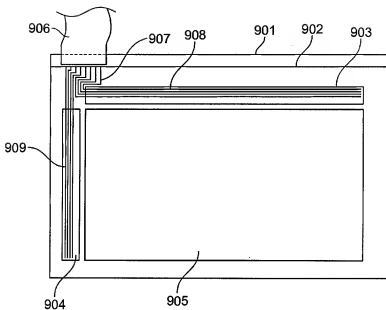


FIG. 5
(Prior Art)